

NTS100P04S



P-Channel Enhancement Mode Trench Power MOSFET

Voltage: -40 Volts

Current: -51.0 Ampers

Package: TO-252

Features

- NH'S Advanced Trench Technology
- Low Rds(on) For Low On-State Loss
- High EAS For High Reliability
- Excellent Qg*Rds(on) Product(FOM)

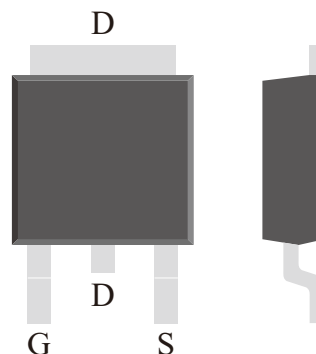
Typical Applications

- DC-DC Converter
- Battery Management System(BMS)
- Printed Circuit Board For Control Circuit
- Uninterruptible Power Supplies(UPS)

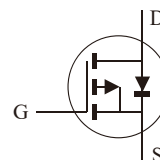
Product Summary

VDS Min.@Tj	-40	V
ID Min.@Ta	-51.0	A
RDS(ON)(TYP)@-10V	10.0	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 °C	I _D	-51.0	A
	Ta= 100 °C		-32.6	
Drain Current-Pulse (Note 1)	Tj< 150 °C	I _{DM}	-204	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25°C	Ta= 25 °C	P _D	60	W
	Ta= 100 °C		24	
Derating Factor		D _F	0.48	W/°C
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	-33.0	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH IAS= -33.0 A,RG= 10.0 Ω Starting Tj=25 °C,VG = -10 V	E _{AS}	272	mJ

Thermal Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	°C
Storage Temperature Range		T _{STD}	-55 to 150	°C
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25 °C	R _{θJA}	62.5	°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	R _{θJC}	2.1	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 13).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=-250uA	BV _{DSS}	-40	--	--	V
Bvdss Temperature Coefficient	ID=-250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.05	--	V/℃
Drain-Source Leakage Current	VDS= -40 V,VGS=0V	I _{DSS}	--	--	-1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= -25.5 A,VDS= -5 V	g _{fs}	--	30.5	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=-250uA	V _{GS(TH)}	-1.0	-1.8	-2.5	V
Drain-Source On Resistance	ID= -25.5 A,VGS= -10.0 V	R _{DS(ON)}	--	10.0	13.9	mΩ
	ID= -25.5 A,VGS= -4.5 V		--	13.0	20.9	
Dynamic Characteristics						
Input Capacitance	VDS= -20 V	C _{iss}	--	4025.0	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	135.0	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	100.0	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.14)						
Turn-On Delay Time	VDS= -20 V	t _{d(on)}	--	12.0	--	ns
Turn-On Rise Time	VGS= -10.0 V	t _r	--	10.0	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	65.0	--	ns
Turn-Off Rise Time		t _f	--	12.0	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.15)						
Total Gate Charge	VDS= -20 V	Q _g	--	70.0	--	nC
Gate-Source Charge	VGS= -10.0 V	Q _{gs}	--	10.0	--	nC
Gate-Drain Charge	ID= -25.5 A	Q _{gd}	--	13.0	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.17)						
Max. Diode Forward Cuurent		I _S	--	--	-51.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	-203.9	A
Diode Forward Voltage	ID= -25.5 A,VGS=0V	V _{SD}	--	-0.67	-1.21	V
Reverse Recovery Time	IS= -25.5 A,di/dt= -100 A/us	t _{rr}	--	26.0	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	30.0	--	nC
Reverse Recovery Current		I _{RRM}	-33.00	-2.3	--	A

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Typical Characteristics Curves

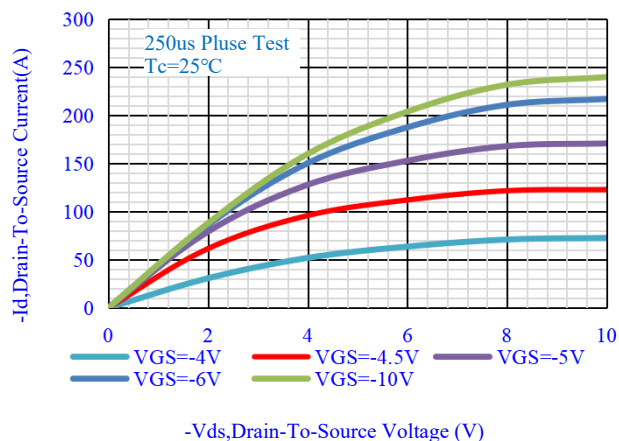


Fig.1-Output Characteristics

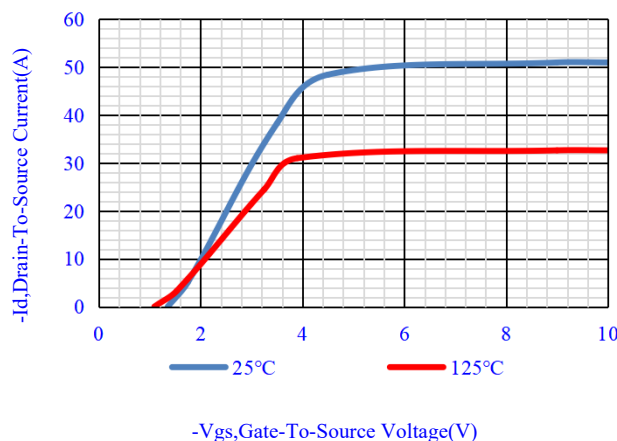


Fig.2-Transfer Characteristics

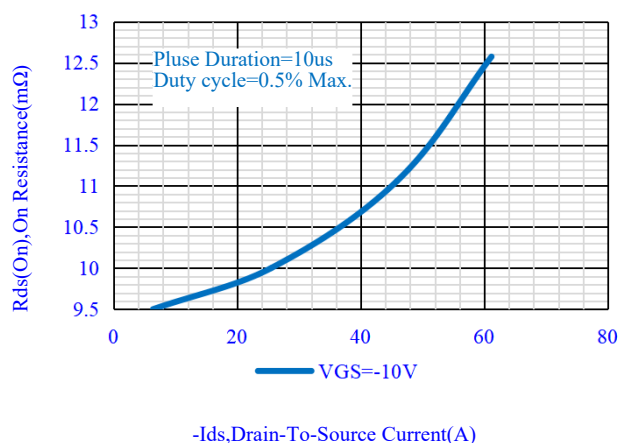


Fig.3-On Resistance Vs. Drain Current

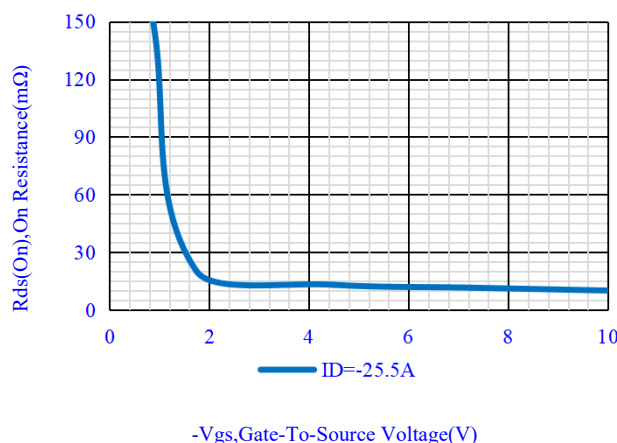


Fig.4-On Resistance Vs. Gate Source Voltage

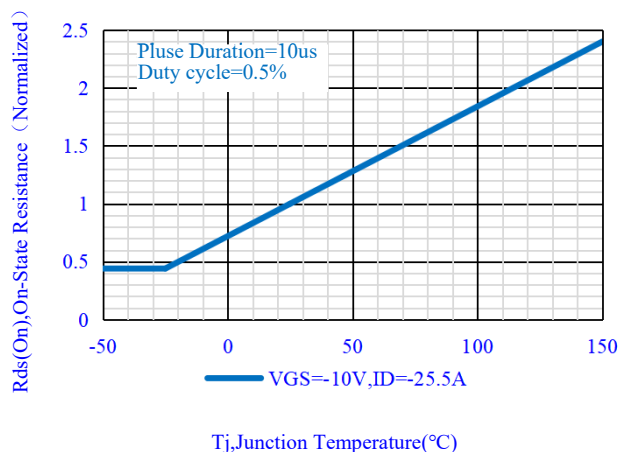


Fig.5-On Resistance Vs. Junction Temperature

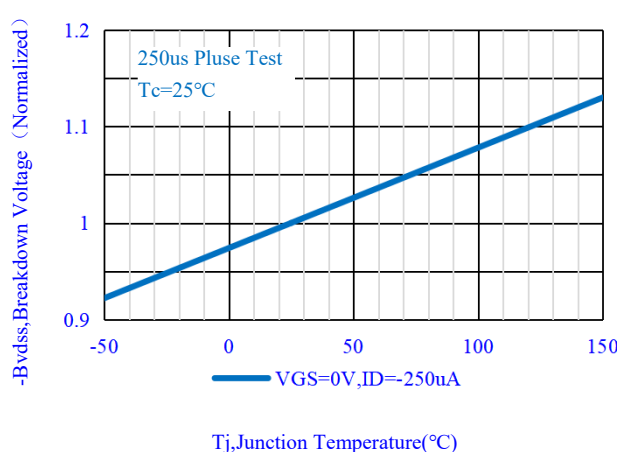


Fig.6-Breakdown Voltage Vs. Junction Temperature

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Typical Characteristics Curves

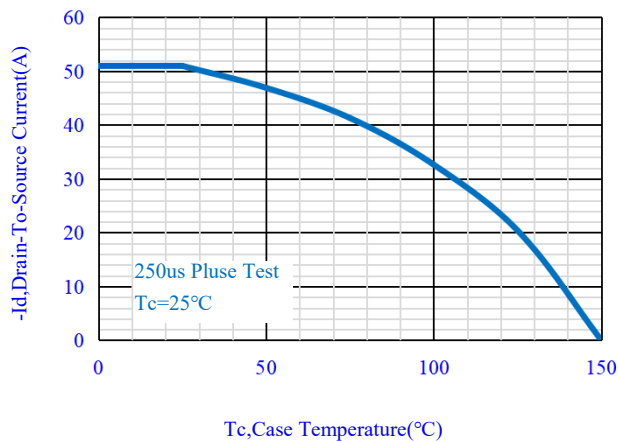


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

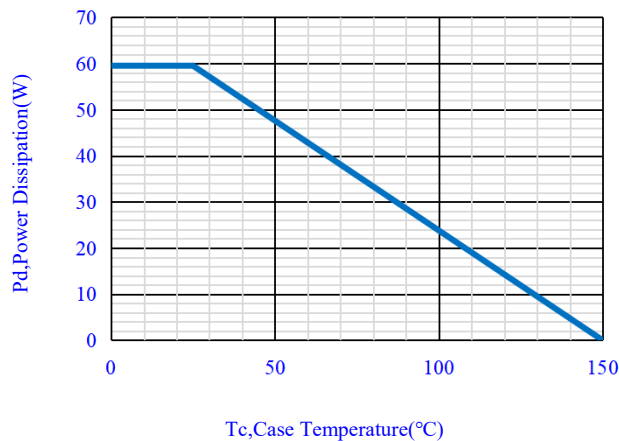


Fig.8-Maximum Power Dissipation Vs. Case Temperature

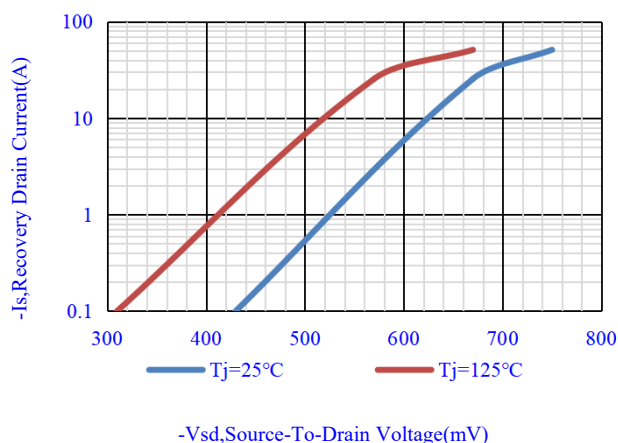


Fig.9-Source-To-Drain Diode Forward Voltage

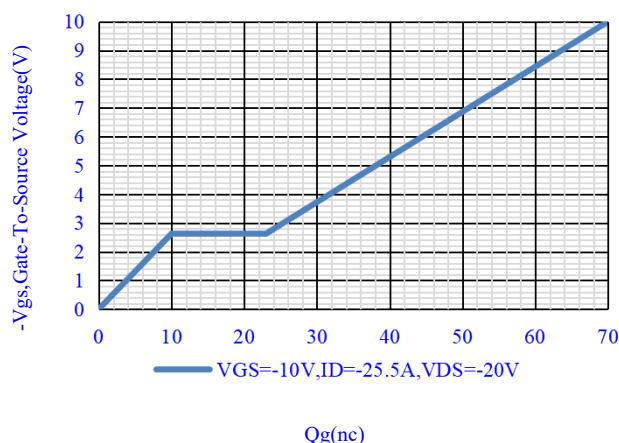


Fig.10-Gate Charge Waveform

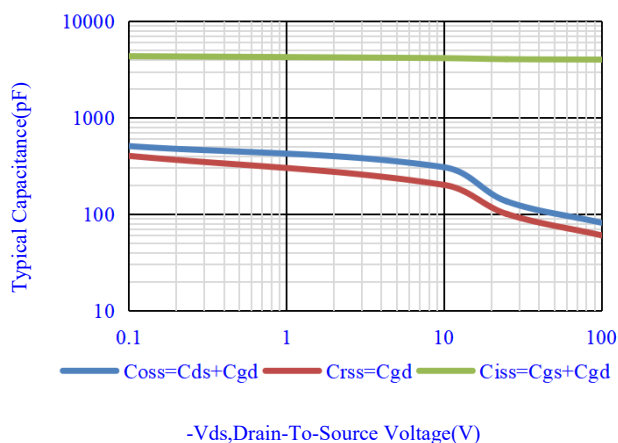


Fig.11-Typical Capacitance Vs. Drain-To-Source Voltage

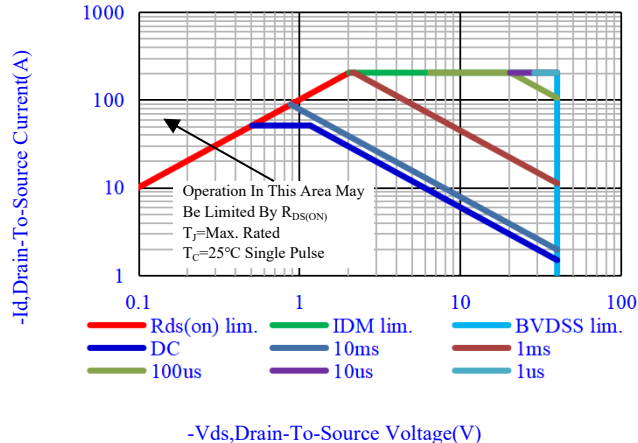


Fig.12-Maximum Safe Operating Area(SOA)

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Typical Characteristics Curves

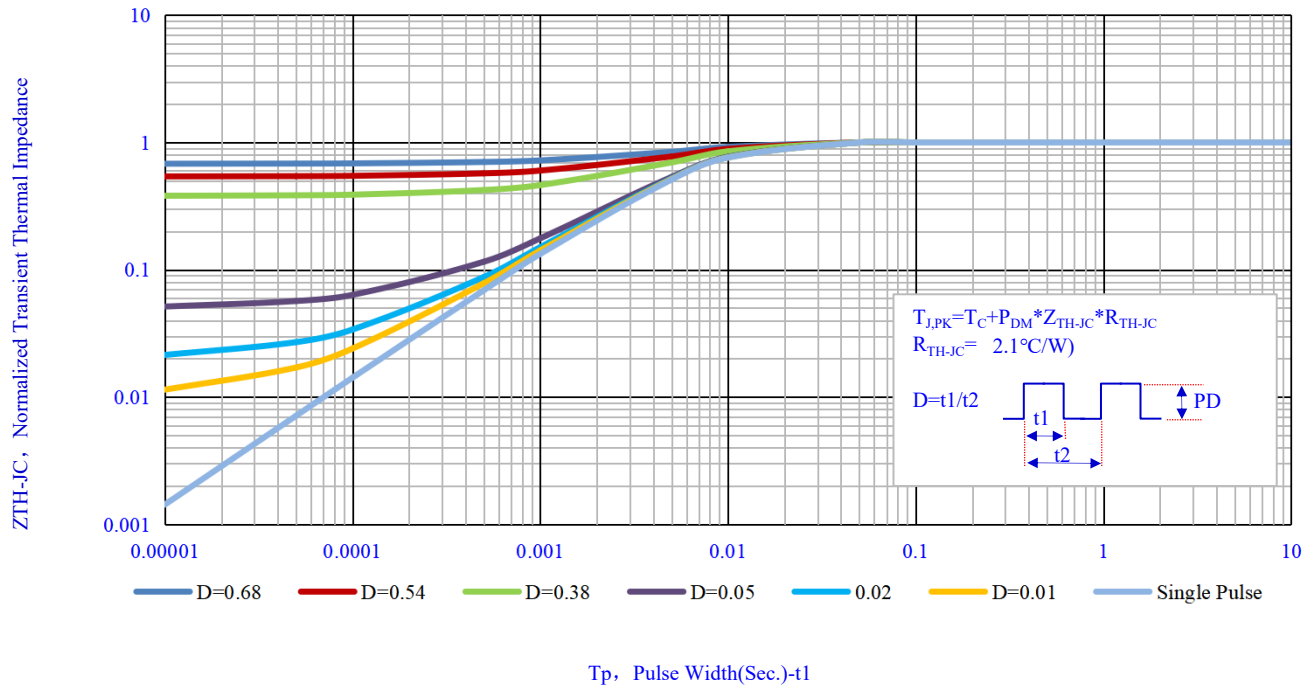


Fig.13- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

Test Circuit & Waveform

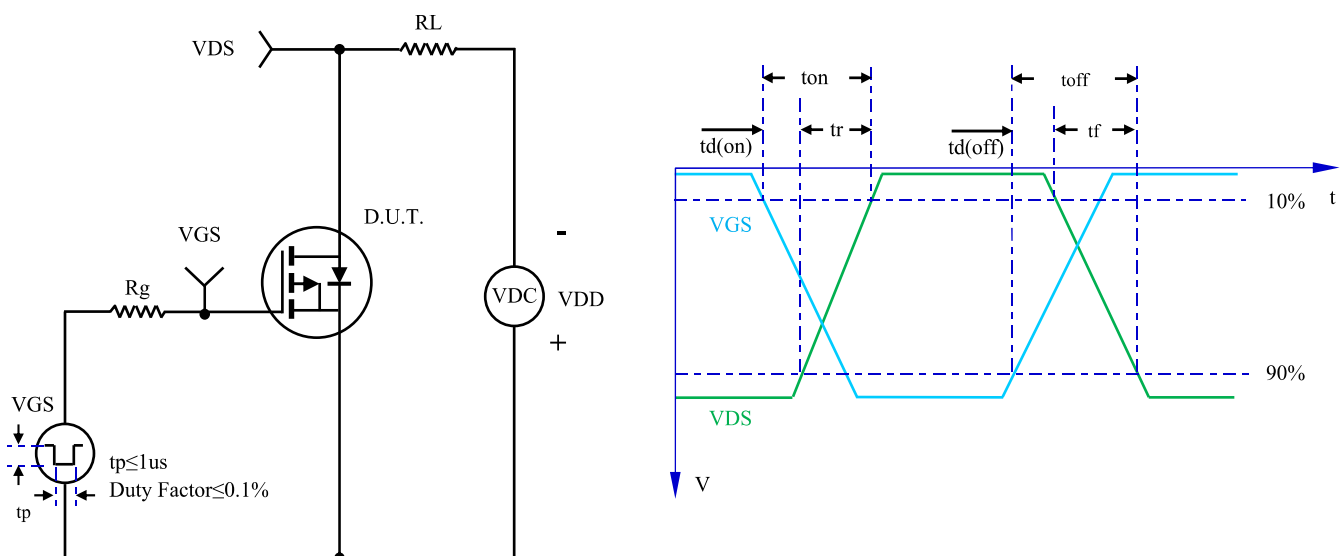


Fig.14- Resistive Switching Test Circuit & Waveform

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Test Circuit & Waveform

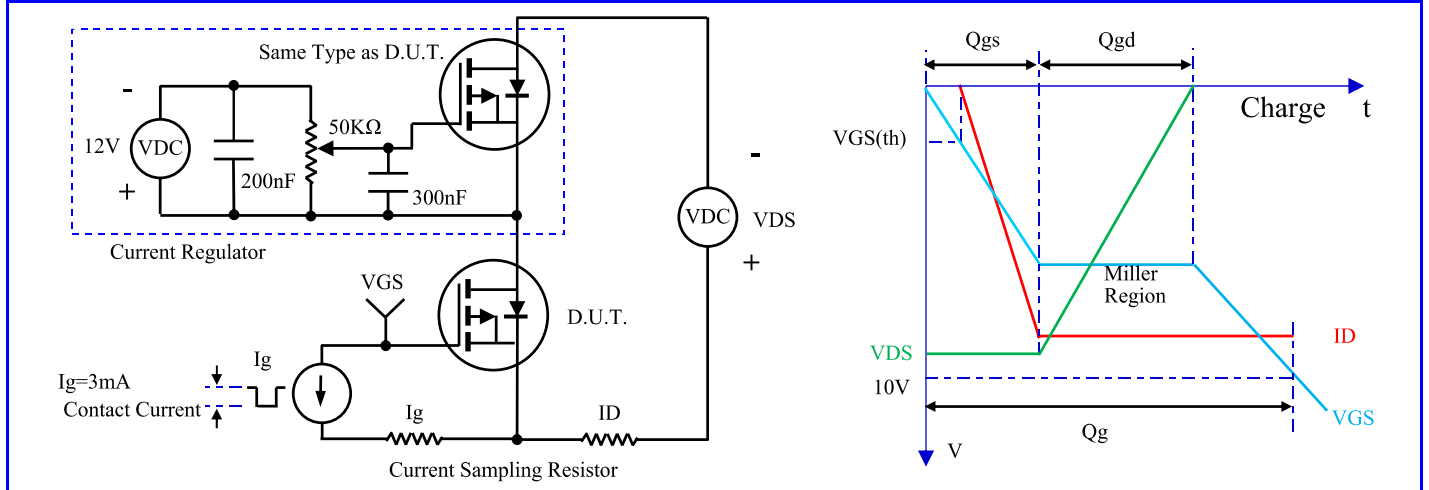


Fig.15- Gate Charge Test Circuit & Waveform

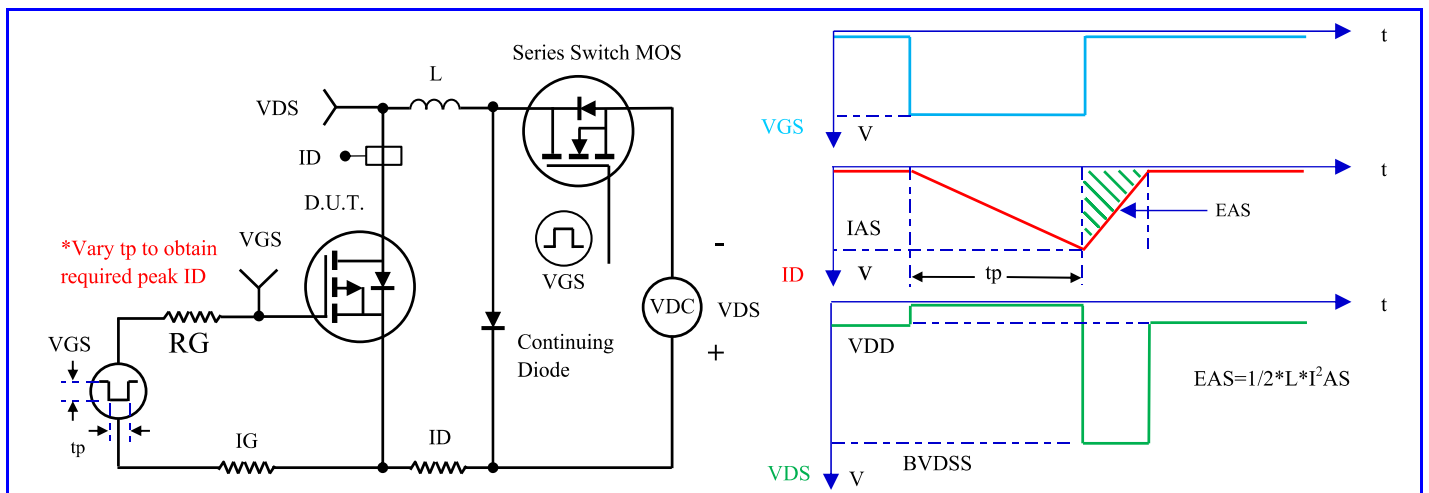


Fig.16- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

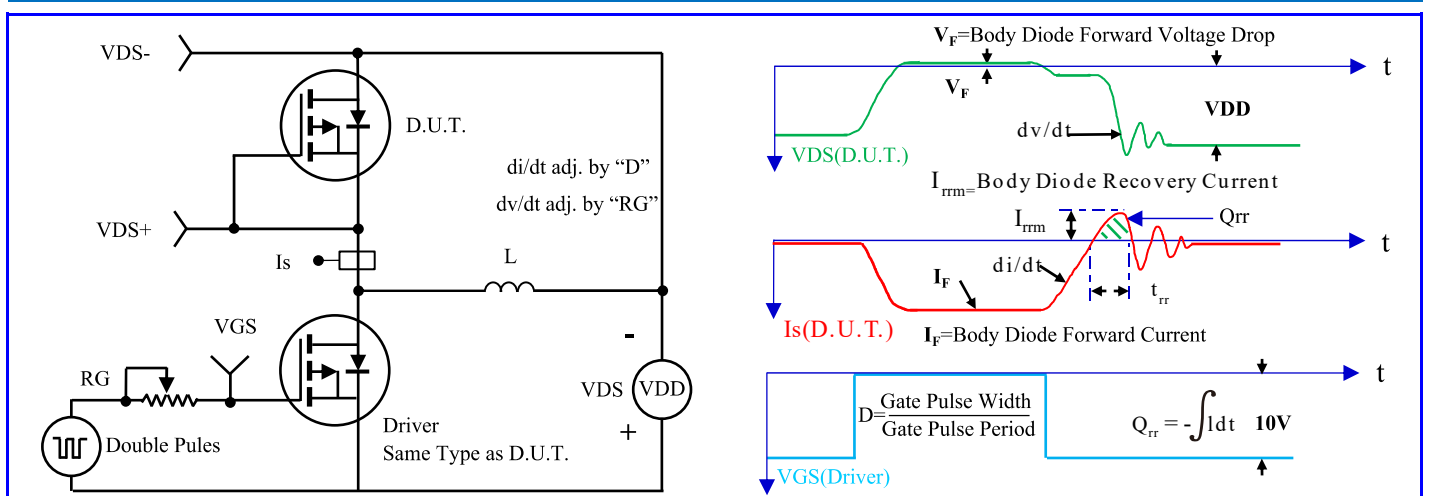


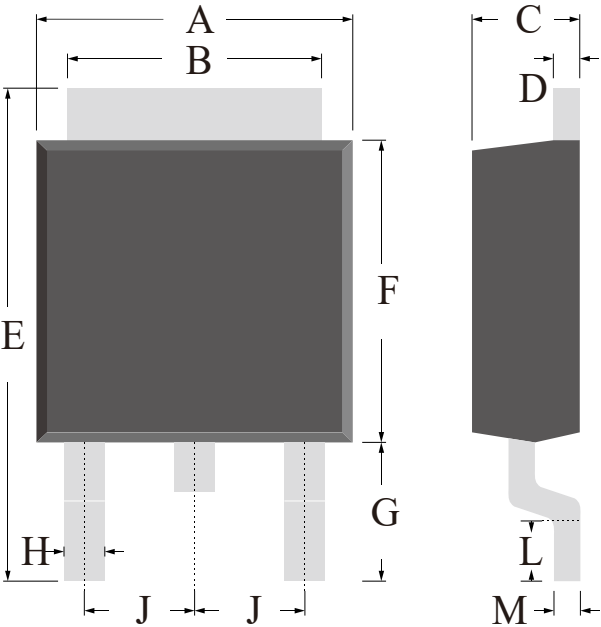
Fig.17- Diode Recovery Test Circuit & Waveform

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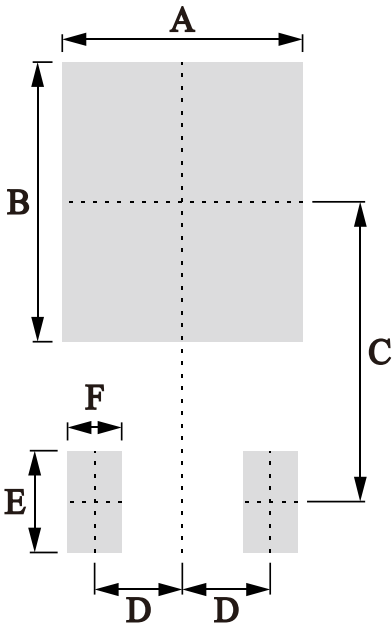
OUTLINE DRAWINGS



TO-252

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.10	-	7.10	0.2402	-	0.2795
B	4.80	-	5.80	0.1890	-	0.2283
C	1.95	-	2.55	0.0768	-	0.1004
D	0.35	-	0.75	0.0138	-	0.0295
E	9.25	-	10.75	0.3642	-	0.4232
F	5.60	-	6.60	0.2205	-	0.2598
G	2.50	-	3.10	0.0984	-	0.1220
H	0.65	-	1.05	0.0256	-	0.0413
J	2.10	-	2.50	0.0827	-	0.0984
L	1.00	-	1.40	0.0394	-	0.0551
M	0.35	-	0.75	0.0138	-	0.0295

RECOMMEDND LAYOUT DRAWINGS



TO-252

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	6.09	-	-	0.2398	-
B	-	7.57	-	-	0.2980	-
C	-	6.64	-	-	0.2610	-
D	-	2.30	-	-	0.0910	-
(33.00)	-	2.76	-	-	0.1090	-
F	-	1.42	-	-	0.0560	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhang Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
NTS100P04S=Model

-000033

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-252	P1	0.321	13" Reel	2500	5000	30000
TO-252	P2	0.321	13" Reel	2500	2500.0	25000.0

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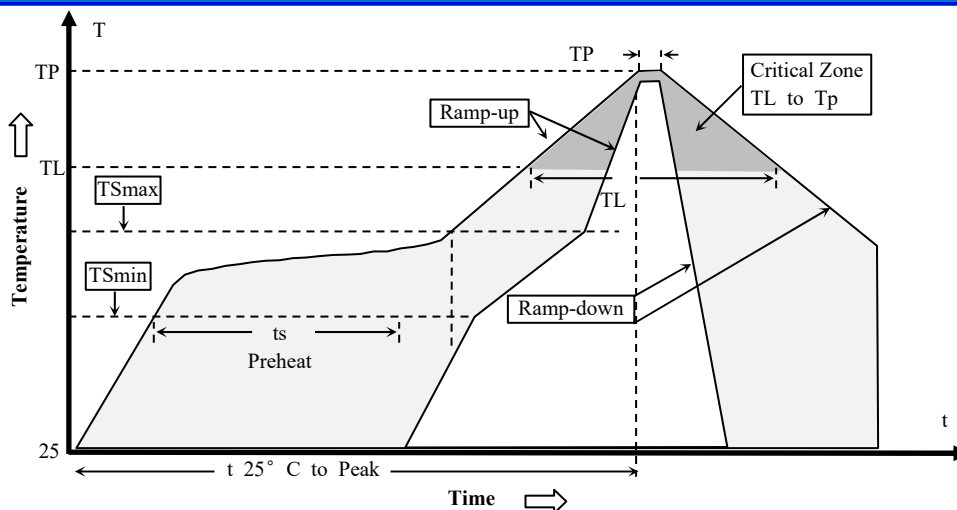
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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat -Temperature Min(T _S min) -Temperature Max(T _S max) -Time(t _s min to t _s max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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